

TECHNICAL DATA DATA SHEET 1026, REV. PRELIMINARY

HERMETIC POWER SCHOTTKY RECTIFIER Ultra Low Reverse Leakage 200°C Operating Temperature

(S-100 for JANTXV equivalent screening; SS for JANS equivalent screening available)

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

MAXIMUM RATINGS

ALL RATINGS ARE @ $T_C = 25$ °C UNLESS OTHERWISE SPECIFIED.

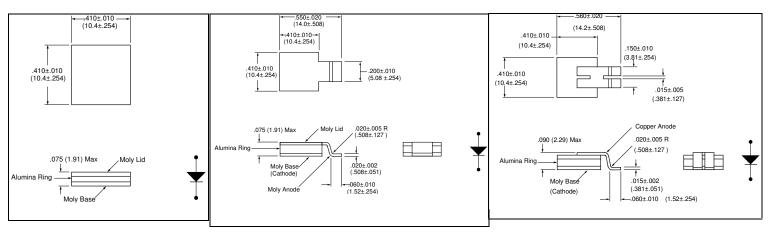
RATING	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	100	Volts
MAXIMUM DC OUTPUT CURRENT (With Cathode Maintained @ T _C = 100 °C)	Io	60	Amps
MAXIMUM NONREPETITIVE FORWARD SURGE CURRENT (t = 8.3ms, Sine)	I _{FSM}	860	Amps
MAXIMUM JUNCTION CAPACITANCE (V _r =5V)	C _T	1500	pF
MAXIMUM THERMAL RESISTANCE (Junction to Mounting Surface, Cathode)	$R\theta_{JC}$	0.35	°C/W
MAXIMUM STORAGE TEMPERATURE RANGE	Tstg	-65 to +175	°C
MAXIMUM OPERATING TEMPERATURE RANGE	Тор	-65 to +200	°C

ELECTRICAL CHARACTERISTICS

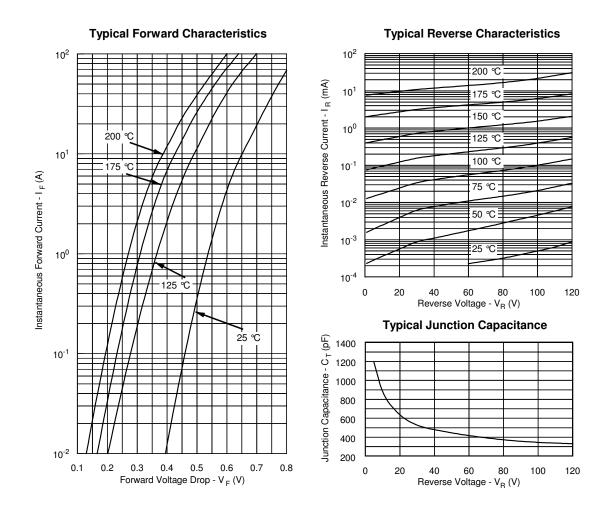
CHARACTERISTIC		SYMBOL	MAX.	UNITS
MAXIMUM FORWARD VOLTAGE DROP, Pulsed $(I_f = 60)$	Amps)			
	T _J = 25 °C	V_{f}	0.87	Volts
	T _J = 125 °C		0.72	
MAXIMUM REVERSE CURRENT (I _r @ 100 V PIV)				
	T _J = 25 °C	I_r	0.03	mA
	T _J = 125 °C		3.0	

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MECHANICAL DIMENSIONS: In Inches / mm



SHD-3A SHD-3B





TECHNICAL DATA

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